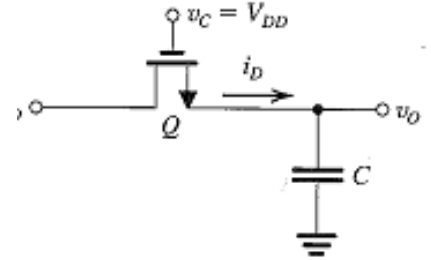


Practice 11: Pass Transistor Logic

Exercise 1: PTL

Consider the following a PTL switch with:

$$\mu_n C_{ox} = 50\mu; \mu_p C_{ox} = 20\mu; |V_{T0}| = 1V; \gamma = 0.5V^{1/2}; \Phi_F = -0.3V; \\ V_{DD} = 5V; (W/L)_n = 4\mu/2\mu; C_L = 50fF$$



- Describe the transient behavior of the circuit when the input goes high at $t=0$ (The output capacitance is initially discharged ($V_{out}(0)=0V$)).
- Describe the transient behavior of the circuit when the input goes low at $t=0$ (The output capacitance is initially charged ($V_{out}(0)=V_{OHmax}$)).
- Find V_{OHmax} for an nMOS with the following properties:
- Find the static current of a cascaded CMOS inverter with:
 $(W/L)_p = 2.5(W/L)_n = 10\mu/2\mu;$
- Find the propagation delay
- Explain two ways to solve the weak '1' problem.

Solution

- The voltage is higher on the left side, setting the Source at the output node.
 - At $t=0$, $V_{DS}=V_{DD}$, and so the transistor is saturated.

$$I_{DS} = \frac{k_n}{2} ((V_{DD} - V_{out}) - V_T)^2$$

- The transistor will stay saturated throughout the charging process, as:

$$V_{DS} = (V_{DD} - V_{out}) > V_{GS} - V_T = (V_{DD} - V_{out}) - V_T$$

We must pay attention that V_T is determined by the body effect:

$$V_T = V_{T0} + \gamma \left(\sqrt{-2\Phi_F + V_{out}} - \sqrt{-2\Phi_F} \right)$$

initially, $V_T=V_{T0}$, but as the capacitor is charged, V_T rises and V_{GS} gets small, causing the current to decrease. This means that the charging is slow.

- The switch closes when $V_{out}=V_{DD}-V_T$, giving us V_{OHmax} . This is very degraded, as V_T is much higher than V_{T0} , due to the body effect. This degrades the noise margin and causes static current in cascaded gates.
- Now the Source and drain have switched sides, as the low voltage is at the input. In this case, $V_{GS}=V_{DD}$ is constant as is $V_{SB}=0$. The nMOS discharges the output to 0 (an nMOS

transfers a strong 0) providing $V_{OLmin}=0$. The current discharge is constantly in the linear region, as:

$$V_{DS} = V_{out} \leq V_{OHmax} = V_{DD} - V_T < V_{GS} - V_T = V_{DD} - V_T$$

- c. V_{OHmax} is the voltage for which the transistor stops conducting, so:

$$V_{OHmax} = V_{DD} - V_T; \quad V_T = V_{T0} + \gamma \left(\sqrt{-2\Phi_F + V_{OHmax}} - \sqrt{-2\Phi_F} \right)$$

$$V_T = V_{T0} + \gamma \left(\sqrt{-2\Phi_F + V_{DD} - V_T} - \sqrt{-2\Phi_F} \right) = 1 + 0.5 \left(\sqrt{5.6 - V_T} - \sqrt{0.6} \right)$$

$$(V_T - 0.61)^2 = 0.25(5.6 - V_T); \quad V_T = 1.6V; \quad V_{OHmax} = 3.4V$$

- d.

1. When the output is low, the nMOS of the inverter is closed, so there is no static power.
2. When the output is high, it is only 3.4V, so $V_{SGp}=1.6V > |V_{Tp}|$, leaving the pMOS open. Since the output is low, V_{SDp} is high, leaving it saturated, giving us:

$$I_{static} = I_{SDp} = \frac{k_p}{2} \left((V_{DD} - V_{OHmax}) - |V_{Tp}| \right)^2 = \frac{1}{2} \cdot 20\mu \cdot \frac{2.5 \cdot 10\mu}{2\mu} (5 - 3.4 - 1)^2 = 18\mu A$$

$$P_{static} = I_{static} \cdot V_{DD} = 90\mu W$$

- e. We will start by finding t_{pLH} as discussed above, finding when the output voltage reaches $V_{DD}/2=2.5V$. To make it easier, we will calculate the average saturation current (that changes due to the body effect:

$$I_{DS}(0) = \frac{k_n}{2} (V_{DD} - V_{T0})^2 = 800\mu A$$

$$V_T(V_{out} = 2.5V) = 1 + 0.5 \left(\sqrt{0.6 + 2.5} - \sqrt{0.6} \right) = 1.49V$$

$$I_{DS}(V_{out} = 2.5V) = \frac{k_n}{2} (V_{DD}/2 - 1.49)^2 = 50\mu A$$

$$I_{Avg} = \frac{800\mu + 50\mu}{2} = 425\mu A = C_L \frac{V_{DD} - V_{DD}/2}{t_{pLH}}$$

$$t_{pLH} = 50f \cdot \frac{2.5}{425\mu} = 0.29nsec$$

Next, we will find t_{pHL} , with the nMOS constantly in linear mode. The initial current is the same as before, and $V_T=V_{T0}$ throughout the discharge, as $V_{SB}=0$:

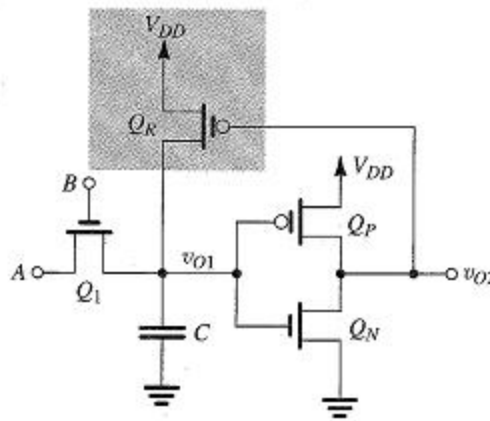
$$I_{DS}(V_{out} = 2.5V) = k_n \left[(V_{DD} - V_{T0}) \frac{V_{DD}}{2} - \frac{1}{2} \left(\frac{V_{DD}}{2} \right)^2 \right] = 690 \mu A$$

$$I_{Avg} = \frac{800 \mu + 690 \mu}{2} = 740 \mu A = C_L \frac{V_{DD} - V_{DD}/2}{t_{pHL}}$$

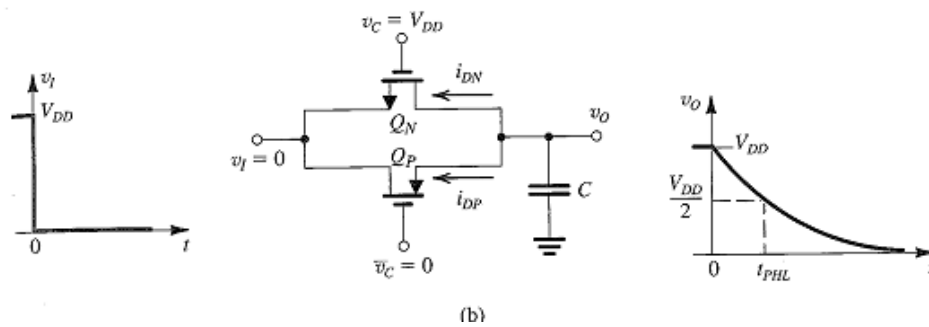
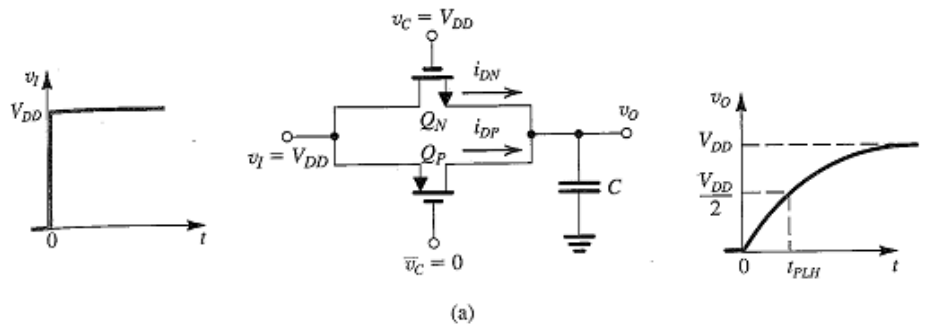
$$t_{pHL} = 50 f \cdot \frac{2.5}{740 \mu} = 0.17 n \text{ sec}$$

$$\text{Altogether, we get } t_{pd} = \frac{t_{pLH} + t_{pHL}}{2} = 0.23 ns$$

f. The first way is to use a pMOS bleed transistor:



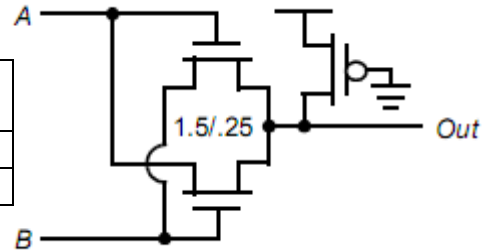
The second way is to use a pass gate:



Exercise 2: Integrating PTL and Pseudo nMOS

The following circuit is given (assume short channel devices):

$V_{DD}=2.5$	$V_{T0} [V]$	$\gamma [\sqrt{V}]$	$V_{DSAT} [V]$	$k' [\frac{\mu A}{V^2}]$	$\lambda [V^{-1}]$
nMOS	0.43	0.4	0.63	115	0.06
pMOS	-0.4	-0.4	-1	30	0.1



- Find the logical function of the gate.
- Size the pMOS to arrive at $V_{OLmin}=0.3V$
- Could the pMOS be removed? What is its job?

Solution

When $A=0$, we receive a Pseudo nMOS inverter with B as the input.

When $B=0$, we receive a Pseudo nMOS inverter with A as the input.

When both A and B are open (or closed), there is no path to ground so $Out=1$.

Our truth table is as follows:

A	B	Out
0	0	1
0	1	0
1	0	0
1	1	1

V_{OHmax} is obviously V_{DD} , but to find V_{OLmin} , we must take one of the states with opposite inputs. Given that the nMOS are the same size, we will take $A=0, B=1$, giving us a Pseudo nMOS inverter with $V_{in}=2.5$. We are to look for k_p that will give us $V_{out}=0.3V$, in which case, the pMOS is velocity saturated and the nMOS is linear:

$$I_{SDp}(sat) = I_{DSn}(lin)$$

$$k_p' \frac{W_p}{L_p} \left[(V_{GSp} - |V_{Tp}|) V_{SDsatp} - 0.5 V_{SDsatp}^2 \right] (1 + \lambda_p V_{SDp}) = k_n' \frac{W_n}{L_n} \left[(V_{GSn} - V_{Tn}) V_{DSn} - 0.5 V_{DSn}^2 \right]$$

$$k_p' \frac{W_p}{L_p} \left[(V_{DD} - |V_{Tp}|) V_{SDatp} - 0.5 V_{SDatp}^2 \right] (1 + \lambda_p (V_{DD} - V_{out})) = k_n' \frac{W_n}{L_n} \left[(V_{DD} - V_{Tn}) V_{out} - 0.5 V_{out}^2 \right]$$

$$30 \mu \frac{W_p}{0.25 \mu} [2.1 \cdot 1 - 0.5] (1 + 0.1(2.5 - 0.3)) = 115 \mu \frac{1.5 \mu}{0.25 \mu} [2.07 \cdot 0.3 - 0.5 \cdot 0.3^2]$$

$$234.24 W_p = 397.44 \mu; \quad W_p = 1.7 \mu m$$

The pMOS pulls up the output when $A=B=0$. Without it the output would be floating!